

# NEC's 7.5 V UHF BAND RF POWER SILICON LD-MOS FET

## NE5511279A

### FEATURES

- **HIGH OUTPUT POWER:**  
 $P_{out} = 40.0 \text{ dBm TYP.}, f = 900 \text{ MHz}, V_{DS} = 7.5 \text{ V},$   
 $P_{out} = 40.5 \text{ dBm TYP.}, f = 460 \text{ MHz}, V_{DS} = 7.5 \text{ V},$
- **HIGH POWER ADDED EFFICIENCY:**  
 $\eta_{add} = 48\% \text{ TYP.}, f = 900 \text{ MHz}, V_{DS} = 7.5 \text{ V},$   
 $\eta_{add} = 50\% \text{ TYP.}, f = 460 \text{ MHz}, V_{DS} = 7.5 \text{ V},$
- **HIGH LINEAR GAIN:**  
 $G_L = 15.0 \text{ dB TYP.}, f = 900 \text{ MHz}, V_{DS} = 7.5 \text{ V},$   
 $G_L = 18.5 \text{ dB TYP.}, f = 460 \text{ MHz}, V_{DS} = 7.5 \text{ V},$
- **SURFACE MOUNT PACKAGE:**  
 $5.7 \times 5.7 \times 1.1 \text{ mm MAX}$
- **SINGLE SUPPLY:**  
 $V_{DS} = 2.8 \text{ to } 8.0 \text{ V}$

### APPLICATIONS

- UHF RADIO SYSTEMS
- CELLULAR REPEATERS
- TWO-WAY RADIOS
- FRS/GMRS
- FIXED WIRELESS

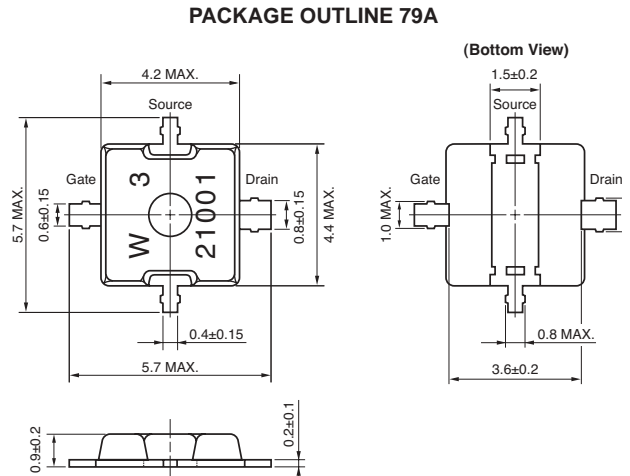
### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT	TEST CONDITIONS
$P_{out}$	Output Power	38.5	40.0	–	dBm	$f = 900 \text{ MHz}, V_{DS} = 7.5 \text{ V},$ $P_{in} = 27 \text{ dBm},$ $I_{DSQ} = 400 \text{ mA (RF OFF)}$
$I_D$	Drain Current	–	2.5	–	A	
$\eta_{add}$	Power Added Efficiency	42	48	–	%	
$G_L$	Linear Gain	–	15.0	–	dB	$P_{in} = 5 \text{ dBm}$
$P_{out}$	Output Power	–	40.5	–	dBm	$f = 460 \text{ MHz}, V_{DS} = 7.5 \text{ V},$ $P_{in} = 25 \text{ dBm},$ $I_{DSQ} = 400 \text{ mA (RF OFF)}$
$I_D$	Drain Current	–	2.75	–	A	
$\eta_{add}$	Power Added Efficiency	–	50	–	%	
$G_L$	Linear Gain	–	18.5	–	dB	$P_{in} = 5 \text{ dBm}$
$I_{GSS}$	Gate to Source Leak Current	–	–	100	nA	$V_{GS} = 6.0 \text{ V}$
$I_{DSS}$	Drain to Source Leakage Current (Zero Gate Voltage Drain Current)	–	–	100	nA	$V_{DS} = 8.5 \text{ V}$
$V_{th}$	Gate Threshold Voltage	1.0	1.5	2.0	V	$V_{DS} = 4.8 \text{ V}, I_{DS} = 1.5 \text{ mA}$
$R_{th}$	Thermal Resistance	–	5	–	$^\circ\text{C/W}$	Channel to Case
$g_m$	Transconductance	–	2.3	–	S	$V_{DS} = 3.5 \text{ V}, I_{DS} = 900 \text{ mA}$
$BV_{DSS}$	Drain to Source Breakdown Voltage	20	24	–	V	$I_{DSS} = 15 \mu\text{A}$

**Notes:**

DC performance is 100% tested. RF performance is tested on several samples per wafer.  
 Wafer rejection criteria for standard devices is 1 reject for several samples.

### OUTLINE DIMENSIONS (Units in mm)



### DESCRIPTION

NEC's NE5511279A is an N-Channel silicon power laterally diffused MOSFET specially designed as the transmission power amplifier for 7.5 V radio systems. Die are manufactured using NEC's NEWMOS1 technology and housed in a surface mount package. This device can deliver 40.0 dBm output power with 48% power added efficiency at 900 MHz using a 7.5 V supply voltage.

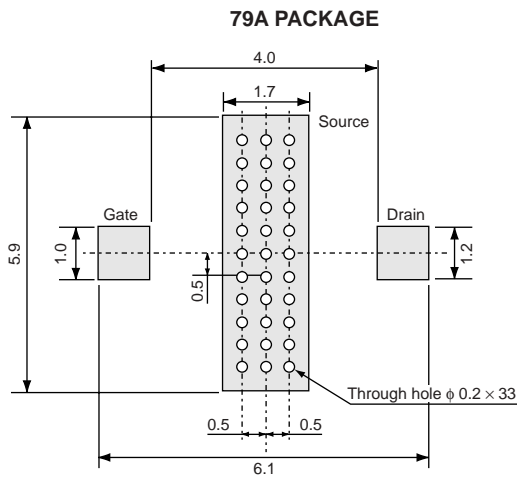
**ABSOLUTE MAXIMUM RATINGS<sup>1</sup>** (T<sub>A</sub> = 25 °C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V <sub>DS</sub>	Drain Supply Voltage <sup>2</sup>	V	20.0
V <sub>GS</sub>	Gate Supply Voltage	V	6.0
I <sub>D</sub>	Drain Current	A	3.0
P <sub>TOT</sub>	Total Power Dissipation	W	20
T <sub>CH</sub>	Channel Temperature	°C	125
T <sub>STG</sub>	Storage Temperature	°C	-55 to +125

Note:

1. Operation in excess of any one of these parameters may result in permanent damage.
2. V<sub>DS</sub> must be used under 12 V on RF operation.

**P.C.B. LAYOUT** (Units in mm)



Note:

Use rosin or other material to prevent solder from penetrating through-holes.

**RECOMMENDED OPERATING LIMITS**

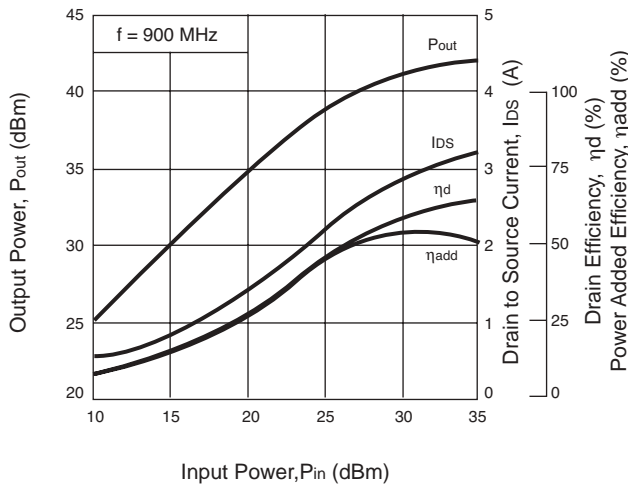
SYMBOLS	PARAMETERS	UNITS	TYP	MAX
V <sub>DS</sub>	Drain to Source Voltage	V	7.5	8.0
V <sub>GS</sub>	Gate Supply Voltage	V	2.0	3.0
I <sub>DS</sub>	Drain Current <sup>1</sup>	A	2.5	3.0
P <sub>IN</sub>	Input Power f = 900 MHz, V <sub>DS</sub> = 7.5 V	dBm	27	30

**ORDERING INFORMATION**

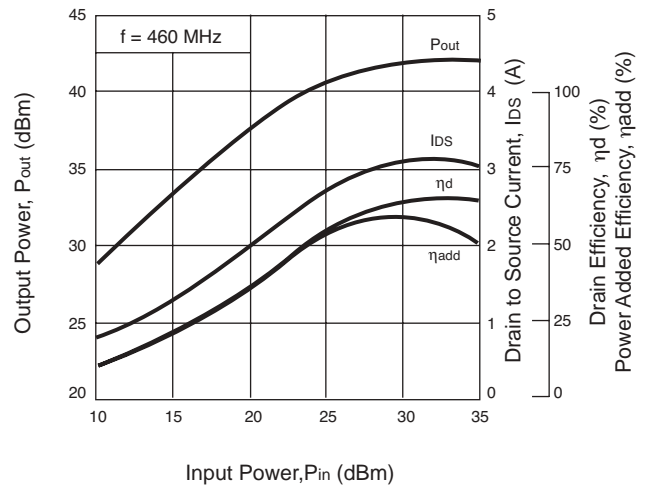
PART NUMBER	QTY
NE5511279A-T1	<ul style="list-style-type: none"> <li>• 12 mm wide embossed taping.</li> <li>• Gate pin faces the perforation side of the tape.</li> <li>• 1 Kpcs/Reel</li> </ul>
NE5511279A-T1A	<ul style="list-style-type: none"> <li>• 12 mm wide embossed taping.</li> <li>• Gate pin faces the perforation side of the tape.</li> <li>• 5 Kpcs/Reel</li> </ul>

**TYPICAL PERFORMANCE CURVES** (T<sub>A</sub> = 25°C)

**OUTPUT POWER, DRAIN CURRENT, η<sub>d</sub>, η<sub>add</sub> vs. INPUT POWER**



**OUTPUT POWER, DRAIN CURRENT, η<sub>d</sub>, η<sub>add</sub> vs. INPUT POWER**



## RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) : 215°C or below Time at temperature of 200°C or higher : 25 to 40 seconds Preheating time at 120 to 150°C : 30 to 60 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) : 260°C or below Time at peak temperature : 10 seconds or less Preheating temperature (package surface temperature) : 120°C or below Maximum number of flow processes : 1 time Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) : 350°C or below Soldering time (per pin of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	HS350-P3

**Caution Do not use different soldering methods together (except for partial heating).**

### Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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